

9097250 TOSHIBA (DISCRETE/OPTO)

90D 16256

DT-33-35



SEMICONDUCTOR

TECHNICAL DATA

MG100G1FL1

MG100G1AL3

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	600	V
Collector-Emitter Voltage	VCEO	600	V
Collector-Emitter Sustaining Voltage	VCEO(SUS)	450	V
Emitter-Base Voltage	VEBO	6	V
Collector Current	DC IC	100	A
	1ms IC	200	
	DC -IC	100	
Base Current	IB	5	A
Collector Power Dissipation (Tc=25°C)	PC	600	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-40~125	°C
Isolation Voltage	VIsol	2500 (AC 1 Minute)	V
Screw Torque	-	30	kg·cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	ICBO	V _{CB} =600V, I _E =0	-	-	2.0	mA	
Emitter Cut-off Current	IEBO	V _{EB} =6V, I _C =0	-	-	400	mA	
Collector-Emitter Sustaining Voltage	V _{CEO(SUS)}	I _C =0.5A, L=40mH	450	-	-	V	
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =100A	100	-	-		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =100A, I _B =2A	-	-	2.0	V	
Base-Emitter Saturation Voltage	V _{BE(sat)}		-	-	2.5	V	
Emitter-Collector Voltage	VECO	I _E =100A, I _B =0	-	-	1.5	V	
Reverse Recovery Time	t _{rr}	-I _C =100A, V _{EB} =3V V _{CE} =300V	-	-	2.0	μs	
Collector Output Capacitance	C _{ob}	V _{CB} =50V, I _E =0 f=1MHz	-	1000	-	pF	
Switching Time	Turn-on Time		-	-	1.0	μs	
	Storage Time		t _{stg}	-	-		12
	Fall Time		t _f	-	-		2.0
Thermal Resistance (Junction to Case)	R _{th(j-c)}	Transistor	-	-	0.208	°C/W	
		Diode	-	-	0.65		

TOSHIBA CORPORATION

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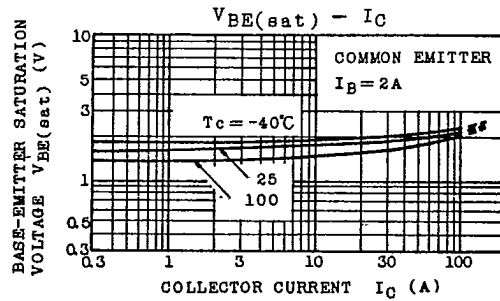
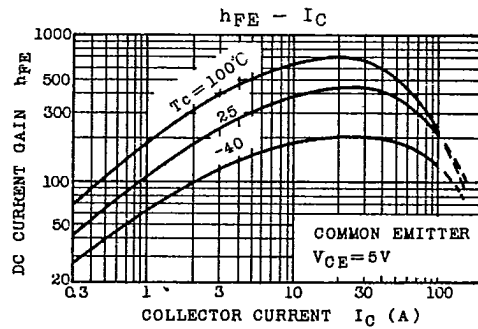
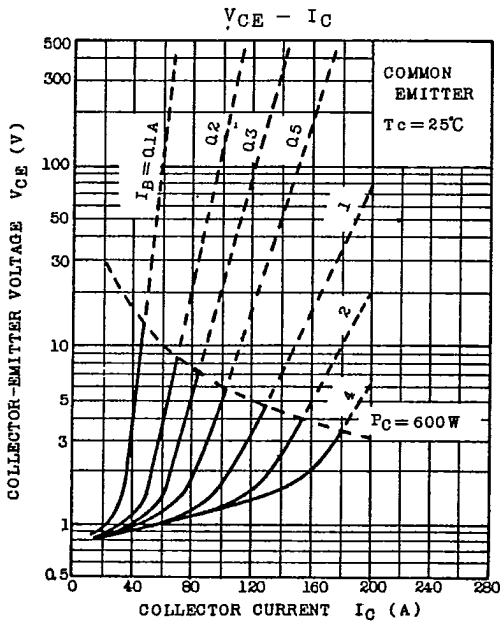
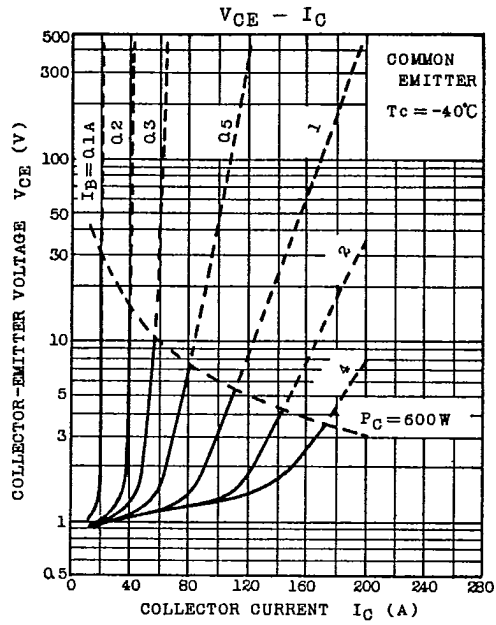
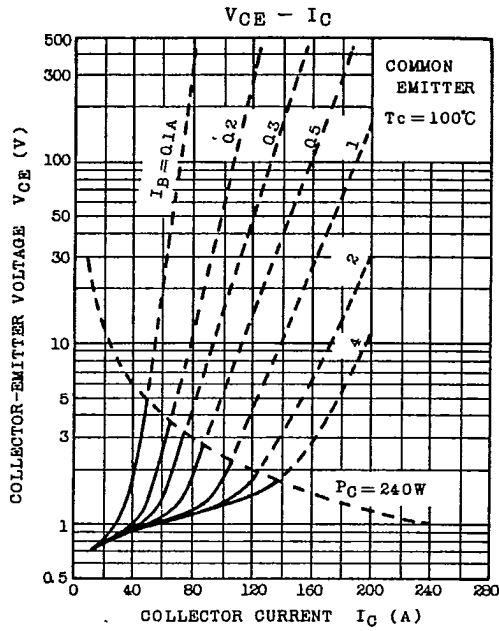
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TOSHIBA CORPORATION

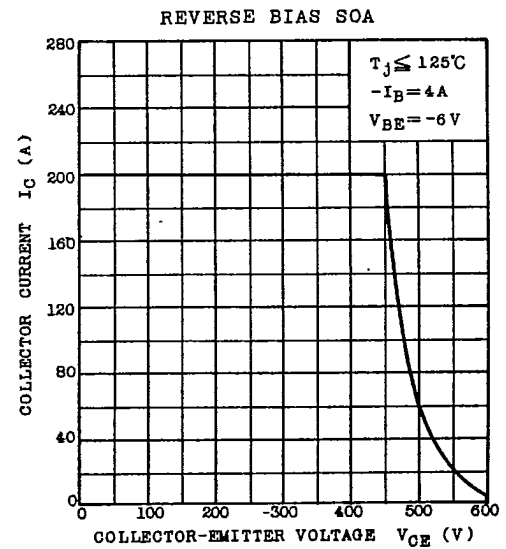
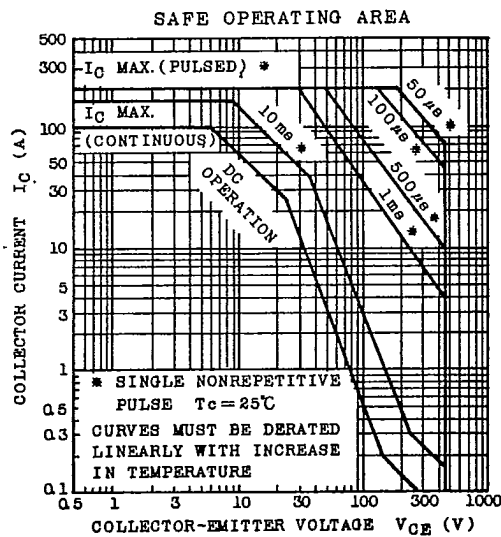
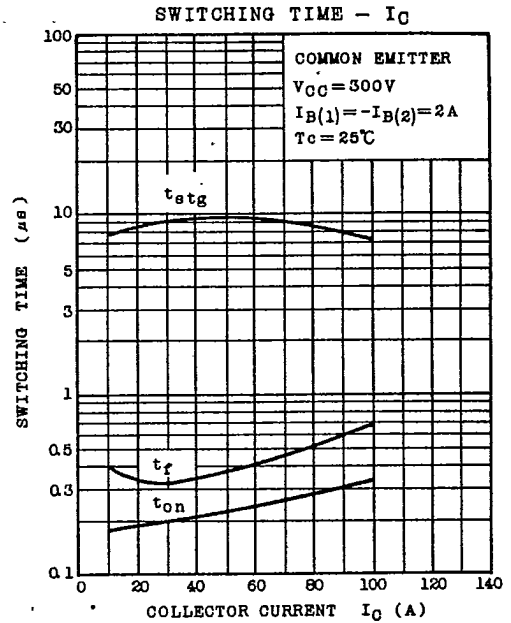
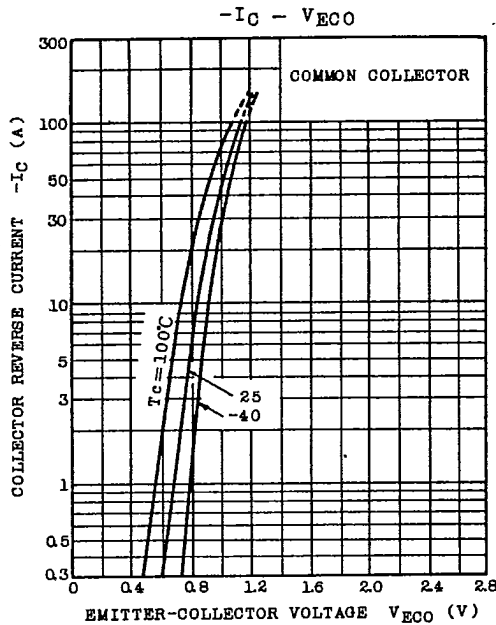
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SEMICONDUCTOR

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TOSHIBA CORPORATION

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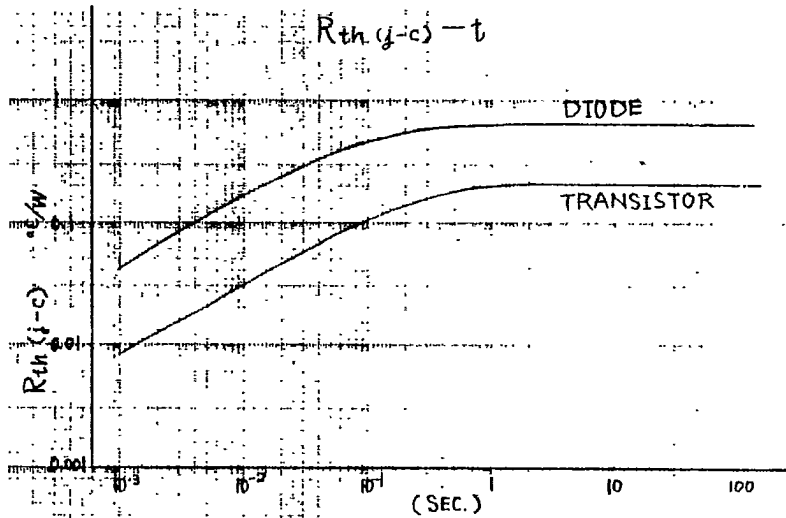
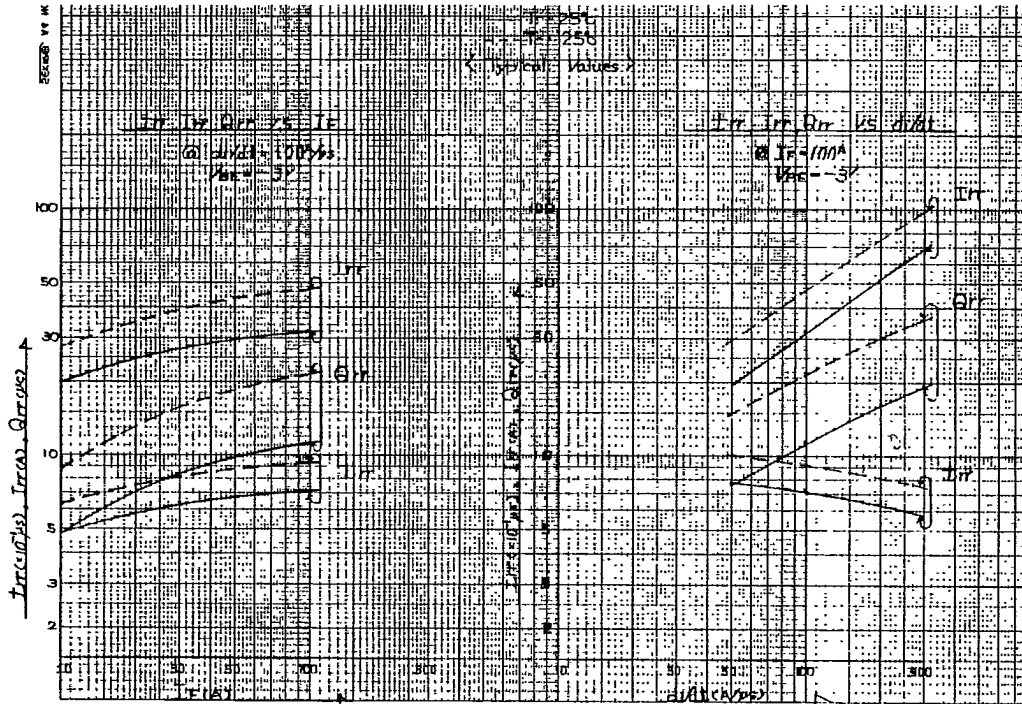


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